ON Semiconductor

Is Now



To learn more about onsemi™, please visit our website at www.onsemi.com

onsemi and ONSEMI. and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/ or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use onsemi products for any such unintended or unauthorized application,

Silicon Carbide Schottky Diode

1700 V, 100 A

NDC100170A, NDCTR100170A

Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

Features

- Max Junction Temperature 175°C
- Avalanche Rated 2045 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery

Applications

- Industrial Motor Loads, Wind Generation Inverter, Solar Inverter, UPS
- Power Switching Circuits

Die Information

• Wafer Diameter: 6 inch

• Die Size: 6140 × 9500 μm (include Scribe Lane)

• Metallization:

◆ Top: Ti/TiN/AISiCu

♦ Back: Ti/NiV/Ag

• Die Thickness: Typ. 200 μm

• Bonding Pad Size:

• Anode: $4260 \times 7620 \mu m$

• Recommended Wire Bond (Note 1)

• Anode: $20 \text{ mil} \times 3$

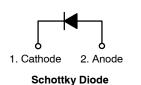
NOTE:

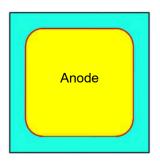
1. Based on TO-247 package



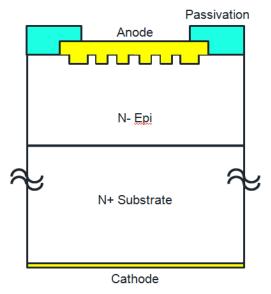
ON Semiconductor®

www.onsemi.com





CROSS SECTION



ORDERING INFORMATION

See detailed ordering and shipping information on page 3 of this data sheet.

ABSOLUTE MAXIMUM RATINGS ($T_J = 25$ °C unless otherwise noted)

| Symbol | Parameter | Value | Unit | |
|-----------------------------------|---|--|-------------|----|
| V_{RRM} | Peak Repetitive Reverse Voltage | | 1700 | V |
| E _{AS} | Single Pulse Avalanche Energy (Notes 2 and 4 | 2025 | mJ | |
| I _F | Continuous Rectified Forward Current @ T _C < | 100 | Α | |
| | Continuous Rectified Forward Current @ T _C < | 135°C | 145 | |
| I _{F, Max} | Non-Repetitive Peak Forward Surge Current | T _C = 25°C, 10 μs | 1435 | А |
| | | T _C = 150°C, 10 μs | 1428 | А |
| I _{F,SM} | Non-Repetitive Forward Surge Current | Half-Sine Pulse, t _p = 8.3 ms | 574 | Α |
| Ptot | Power Dissipation | T _C = 25°C | 1666 | W |
| | | T _C = 150°C | 277 | W |
| T _J , T _{STG} | Operating and Storage Temperature Range | • | -55 to +175 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

2. E_{AS} of 2025 mJ is based on starting T_J = 25°C, L = 0.5 mH, I_{AS} = 90 A, V = 50 V.

3. I_{FMax}, and I_{FSM} surge test value are limited by measurement limitation, it's not product capability

4. DC, E_{AS} and Curve test result base on TO247 package

THERMAL CHARACTERISTICS

| Symbol | Parameter | Value | Unit |
|----------------|---|-------|------|
| $R_{	heta JC}$ | Thermal Resistance, Junction to Case, Max | 0.09 | °C/W |

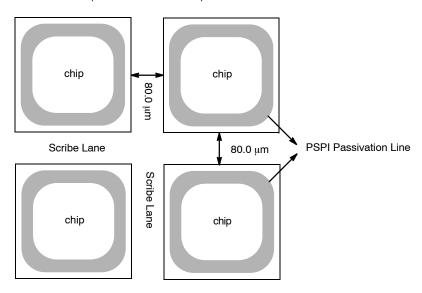
ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

| Symbol | Parameter | Test Condition | Min | Тур | Max | Unit |
|----------------|-------------------------|---|-----|------|-----|------|
| V _F | Forward Voltage | I _F = 100 A, T _J = 25°C | - | 1.6 | _ | V |
| | | I _F = 100 A, T _J = 125°C | - | 2.16 | _ | |
| | | I _F = 100 A, T _J = 175°C | - | 2.6 | - | |
| I _R | Reverse Current | V _R = 1700 V, T _J = 25°C | - | 0.15 | 40 | μΑ |
| | | V _R = 1700 V, T _J = 125°C | - | 1.45 | 60 | |
| | | V _R = 1700 V, T _J = 175°C | - | 12.3 | 100 | |
| Q_C | Total Capacitive Charge | V = 800 V | - | 604 | - | nC |
| С | Total Capacitance | V _R = 1 V, f = 100 kHz | - | 7672 | - | pF |
| | | V _R = 400 V, f = 100 kHz | _ | 539 | - | |
| | | V _R = 800 V, f = 100 kHz | _ | 383 | _ | |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

The Configuration of Chips

(Based on 6 inch Wafer)



Sawn-on-film frame packing based on tested wafer

ORDERING INFORMATION

| Part Number | Die Size with SL (μm) | Package | Shipping |
|--------------|-----------------------|---------|-------------|
| NDC100170A | 6140*9500 | N/A | Wafer Sales |
| NDCTR100170A | 6140*9500 | N/A | Tape & Reel |

TYPICAL CHARACTERISTICS ($T_J = 25^{\circ}C$ unless otherwise noted)

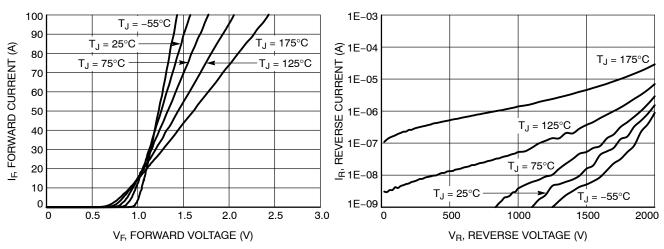


Figure 1. Forward Characteristics

Figure 2. Reverse Characteristics

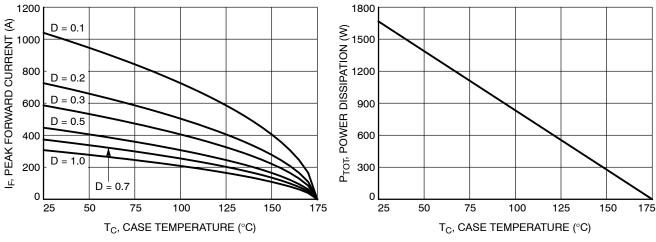


Figure 3. Current Derating

Figure 4. Power Derating

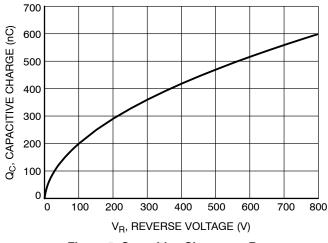


Figure 5. Capacitive Charge vs. Reverse Voltage

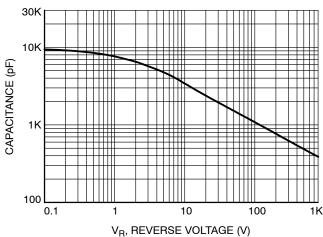


Figure 6. Capacitance vs. Reverse Voltage

TYPICAL CHARACTERISTICS (T_{.1} = 25°C unless otherwise noted)

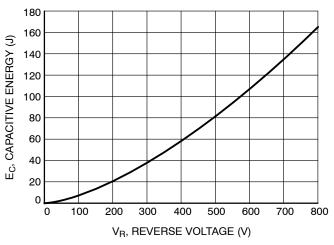


Figure 7. Capacitance Stored Energy

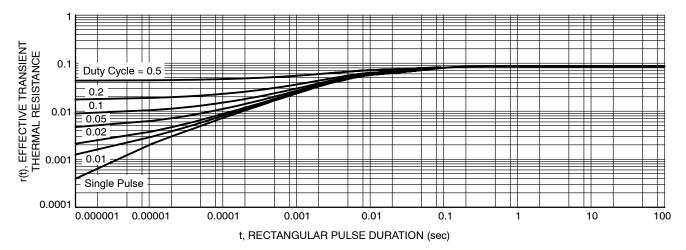


Figure 8. Junction-to-Case Transient Thermal Response

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices with a same or similar classification in a foreign jurisdiction or any devices with a same or similar classification in a foreign jurisdiction or any devices with a same or similar class

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

ON Semiconductor Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative